

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	3346	semiconductor and (phase adj shift adj mask)	US- PGPUB; USPAT; EPO; JPO; DERWEN T
2	BRS	L2	1763	semiconductor and ((phase adj shift adj mask) with (pattern or patterned or patterning))	US- PGPUB; USPAT; EPO; JPO; DERWEN T
3	BRS	L3	69	2 and EEPROM	US- PGPUB; USPAT; EPO; JPO; DERWEN T
4	BRS	L4	991	257/321.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T
5	BRS	L6	482	257/317.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T

	Type	L #	Hits	Search Text	DBs
6	BRS	L7	461	L6 not L5	US- PGPUB; USPAT; EPO; JPO; DERWEN T
7	BRS	L8	816	L4 and tunnel\$	US- PGPUB; USPAT; EPO; JPO; DERWEN T
8	BRS	L9	4687	257/314,315,316,317,321,326 .ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T
9	BRS	L10	122	L9 and (tunnel\$ adj window)	US- PGPUB; USPAT; EPO; JPO; DERWEN T
10	BRS	L12	17	("5293331").URPN.	USPAT
11	BRS	L5	115	L4 and (select adj gate)	US- PGPUB; USPAT; EPO; JPO; DERWEN T

	Type	L #	Hits	Search Text	DBs
12	BRS	L11	109	L10 not L5	US- PGPUB; USPAT; EPO; JPO; DERWEN T